

8 Diode

Switching

★Under Development

Type No	Maximum Ratings				Electrical Characteristics (Ta = 25°C) MAX						Package	Fig
	V _{RM} (V)	I _{FM} (mA)	I _O (mA)	P (mW)	V _F (V)	I _R MAX		C _T f:1MHz (pF)	V _R (V)	t _{rr} (ns)	MAX	Condition
						I _F (mA)	V _R (V)					
KDS1553	70				1.4	100	60	3.5				
KDS1554	55	300	100	300			50					
KDS1555	35						30					
IN4148	75	225	100	500	1.0	10	20	4.0				
KDS176	35	300	100	300	1.2	100	30	3.0				
KDS181S												
KDS184S												
KDS187S												
KDS190S	80	300	100	150	1.2	100	80	3.0		4		
KDS193S												
KDS196S												
★KDS226S												
KDS200												
KDS201				200				4.0				
★KDS227												

 $V_R = 6V$
 $R_L = 100\Omega$
 $I_F = 10mA$

Temperature Bias Compensation

Type No	V _R (V)	I _{FM} (mA)	I _{FAV} (mA)	T _J (mA)	V _F			I _R		V _F		Package	Fig
					MIN (V)	TYP (V)	MAX (V)	I _F (mA)	MAX (μ A)	V _R (V)	TYP mV/°C		
KS8513A-0	5	150	50	150	0.63	0.65	0.68	3	10	5	-2.0	DO-35	F37

T-01-01

AFC diode

★Under Development

Type No	V _R (V)	T _J (°C)	I _R (nA)	MAX		C _r				K		Q f=50MHZ		Package	Fig
				V _R (V)	I _R (nA)	MIN (PF)	MAX (PF)	VR (V)	f (MHZ)	MIN	MAX	TYP	V _r (V)		
★KDV147	15	125	50	15		11.7	13.7	8	1	—	—	—	—	TO-92M(C)	F5
★KDV149	15	125	50	15		—	30	8	1	—	—	450	1	TO-92M	F39
KDS2236	15	150	100	4		7	14	4	1	0.21	0.5	120	4	DO-35	F37

Schottky Barrier Diode

Type No	V _{RRM} (V)	I _{FRM} (A)	I _{FSM} (A)	I _{F(AV)} (A)	T _J (°C)	V _{F(Max)} (V) I _O =15A	I _R (Tc=25°C) (mA)	R _{th(J-C)} °C/W	R _{th(J-A)} °C/W	Package	Fig
KDB1545	45	15	150	7.5	-65~+150	0.70	0.1	3.0	60	TO-220AB(b)	F6

Rectifier

Type No	V _{RM} (V)	V _{RRM} (V)	I _O (A)	I _{SURGE}	T _J (°C)	T _{stg} (°C)	V _F (V)	MAX I _F (A)	I _R (μA)	MAX V _{RM} (V)	Package	Fig
IN4001	50	100	1	50	175	-65~175	1.1	1	10	RATED	DO-41	F36
IN4002	100	200		50								
IN4003	200	300		50								
IN4004	400	500		50								
IN4005	600	750		30								
IN4006	800	1000		30								
IN4007	1000	1200		30								